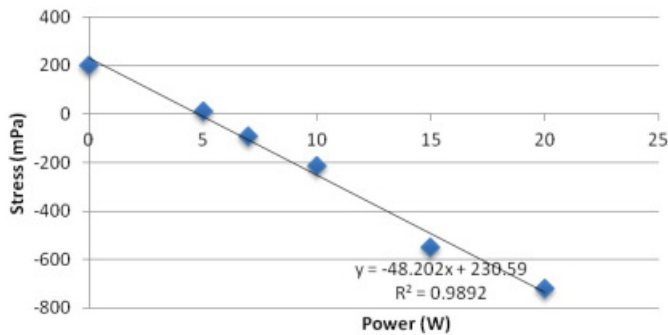


DES Silicon Nitride

This process will deposit PECVD nitride using DES.

Material	SiO ₂
Substrate Size	Die to 8" (200mm)
Deposition Rate	>600 Å /min
Uniformity	<5 %
Refractive Index	1.95-2.0 ±0.05
Step Coverage	Conformal
Stress	Slightly Tensile
Reproducibility	<± 2.5%

Additional stress control can be achieved by adding the Triode option.



Triode mode stress control. (HF fixed, LF varied)

For more information, contact:

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